

/ Descriptions

TO-220 PNP Silicon PNP transistor in a TO-220 Plastic Package.

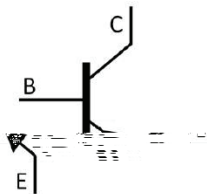
/ Features

Complementary to 2SC2562,
Low collector saturation voltage, high speed switching time, complementary to 2SC2562.

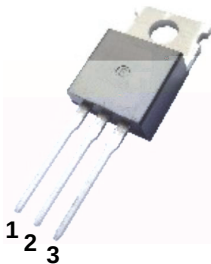
/ Applications

High current switching applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

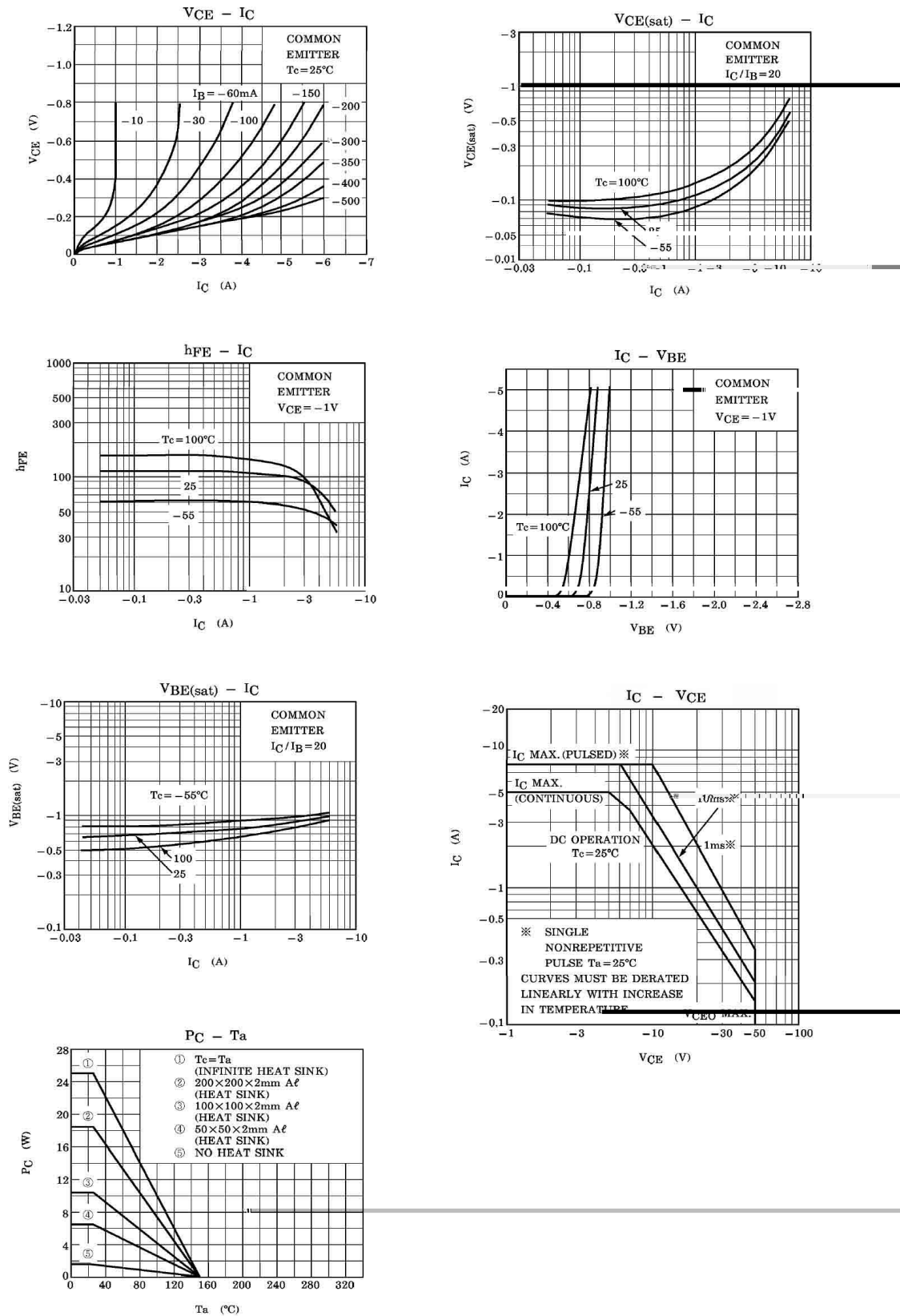
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	O	Y
h_{FE} Range	70~140	120~240

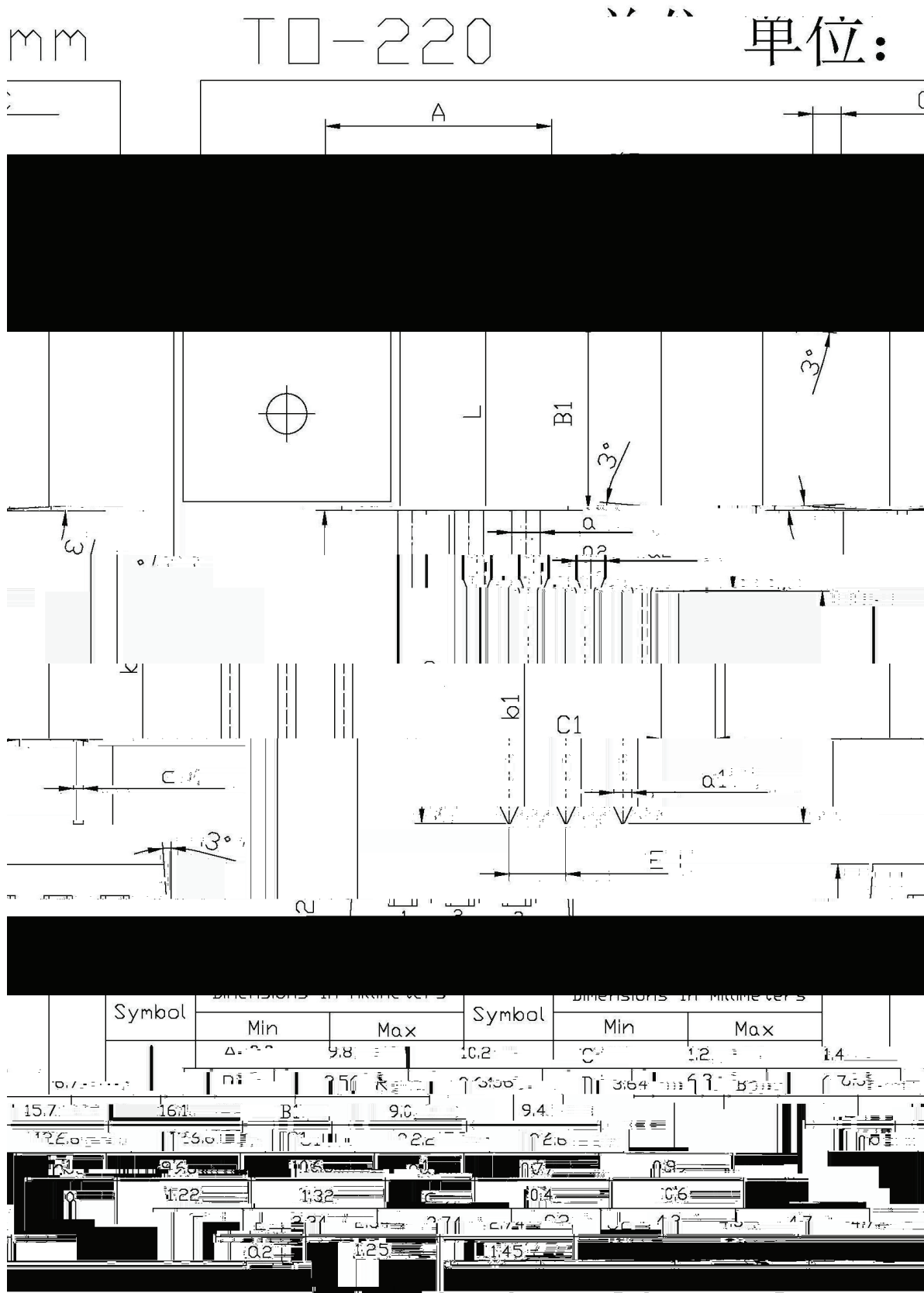
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-50	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-5.0	A
Collector Power Dissipation	P_C	2.0	W
	$P_C(T_C=25^{\circ}C)$	25	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55~150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown V						

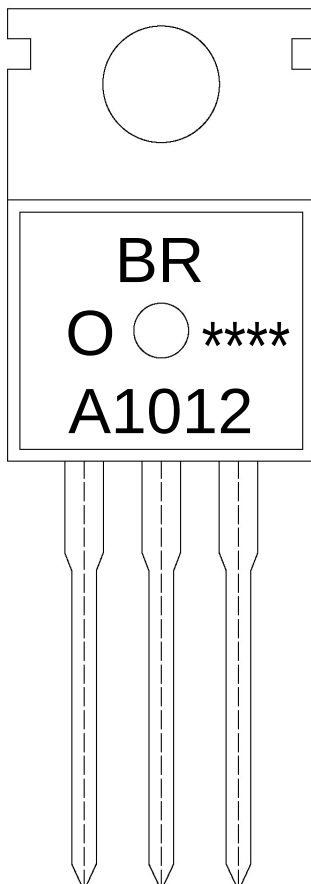
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

A1012

O: h_{FE}

Note:

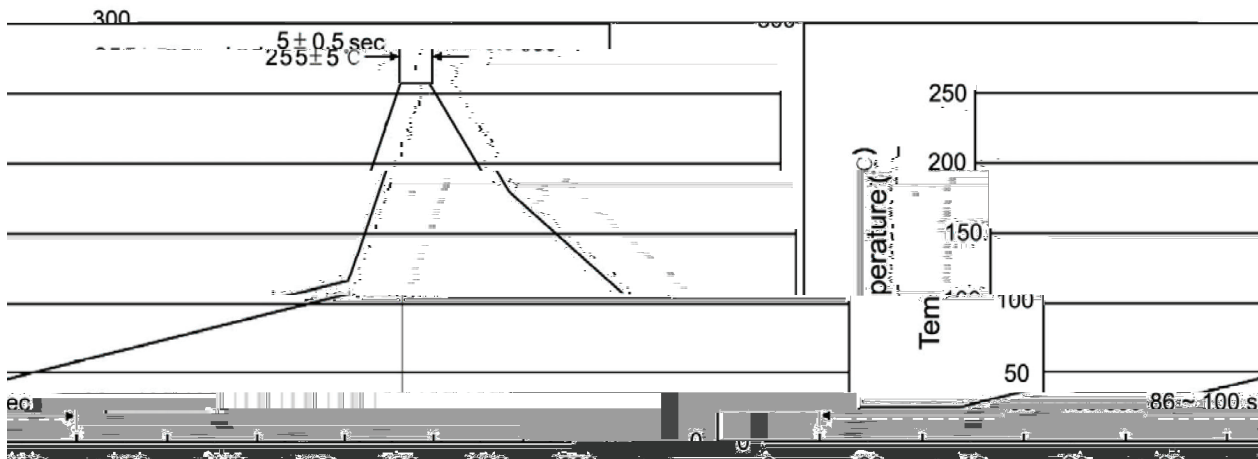
BR: Company Code

A1012: Product Type.

O: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.

() / **Temperature Profile for Dip Soldering(Pb-Free)**



Note:

- | | | | | | |
|---|-------|-----|-----------|---|--------------------------------------|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | | 5±0.5sec; | 2.Peak Temp.:255±5 , Duration:5±0.5sec. | |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ **Resistance to Soldering Heat Test Conditions**

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ **Packaging SPEC.**

/ **BULK**

Package Type 封装形式	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units 包装数量 Units/Inner Box 只/盒	Dimension 包装尺寸 (unit: mm ³)
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